

Description

The IRFR5305T uses advanced trench technology to

provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



TO252-2L

General Features

V_{DS} =- 60V, I_D =-20A

 $R_{DS(ON)} < 72m\Omega$ @ $V_{GS}=-10V$

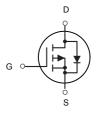
 $R_{DS(ON)}$ < 100m Ω @ V_{GS} =-4.5V

Application

PWM applications

Load switch

Power management



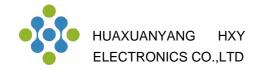
P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRFR5305T	TO252-2L	20P06 XXYYYY	2500

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	±20	V
I _D (25°C)		-20	А
I _D (70°C)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-15	А
IDM		-48	А
Po	Maximum Power Dissipation	40	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	20	°C/W



ELECTRICAL CHARACTERISTICS (TA=25 °C unless otherwise noted)

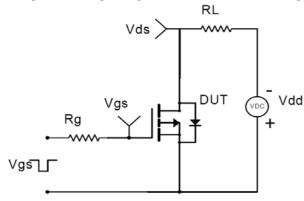
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BVpss	V _{GS} =0V I _D =-250μA	-60			V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-48V,V _{GS} =0V			-1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS} (th)	Vos=Vgs, lo=-250µA	-1	-1.8	-2.5	V
		Vss=-10V, ID=-10A		64	72	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =-4.5V, I _D =-10A		90	100	mΩ
Forward Transconductance	grs	V _{DS} =-5V, I _D =-20A	5			S
Input Capacitance	Clss			2460		PF
Output Capacitance	Coss	V _{DS} =-30V,V _{GS} =0V, F=1.0MHz		220		PF
Reverse Transfer Capacitance	Crss	F = 1.0IVII 12		155		PF
Turn-on Delay Time	td(on)			14		nS
Turn-on Rise Time	t _r	V _{DS} =-30V,V _{GS} =-		20		nS
Turn-Off Delay Time	td(off)	- 10V,R _{GEN} =3Ω I_D =1A		40		nS
Turn-Off Fall Time	t _f			19		nS
Total Gate Charge	Qg			48		nC
Gate-Source Charge	Qgs	- V _{DS} =-30V,I _D =-20A,V _{GS} =-10V		11		nC
Gate-Drain Charge	Qgd	-		10		nC
Body Diode Reverse Recovery Time	Trr	I _F =-20A, dI/dt=100A/μs		40		nS
Body Diode Reverse Recovery Charge	Qrr	1120A, 41/41-100A/µS		56		nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =-1A		-0.72	-1	V

NOTES:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on 1in² FR4 Board, t ≤ 10 sec.
 Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%. 4. Guaranteed by design, not subject to production testing.



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



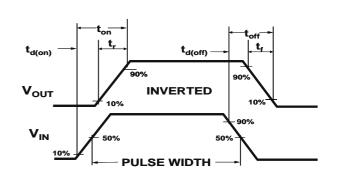


Figure 1:Switching Test Circuit

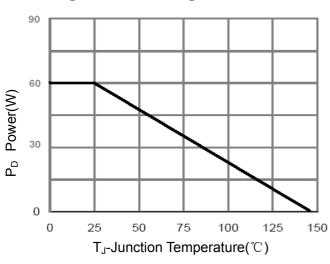


Figure 2:Switching Waveforms

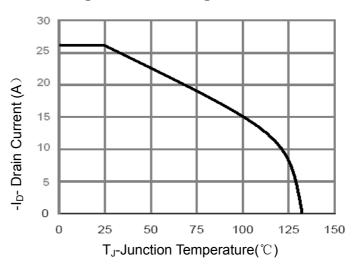


Figure 3 Power Dissipation

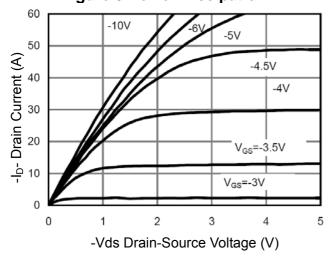


Figure 4 Drain Current

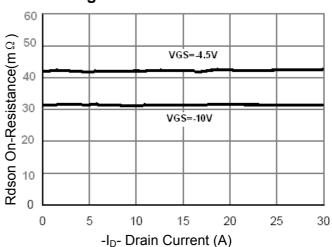


Figure 5 Output CHARACTERISTICS

Figure 6 Drain-Source On-Resistance

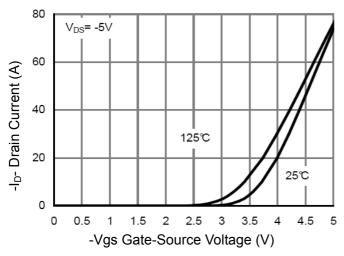


Figure 7 Transfer Characteristics

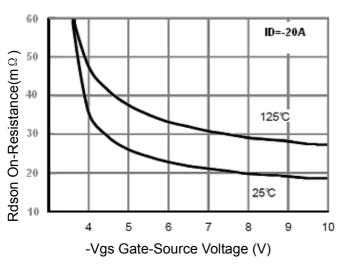


Figure 9 Rdson vs Vgs

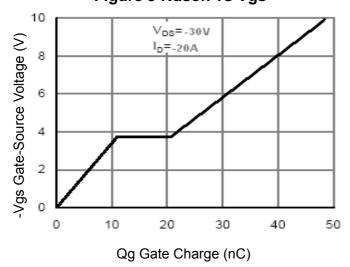


Figure 11 Gate Charge

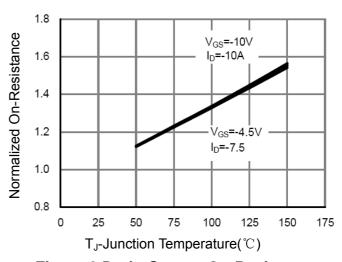


Figure 8 Drain-Source On-Resistance

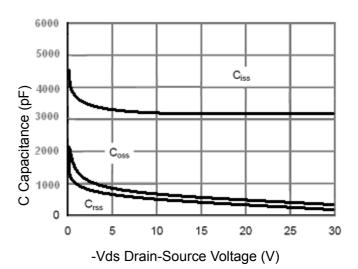


Figure 10 Capacitance vs Vds

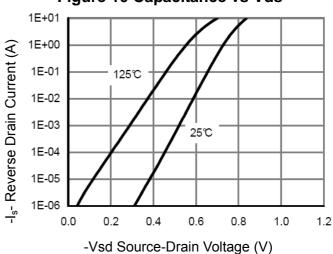


Figure 12 Source- Drain Diode Forward



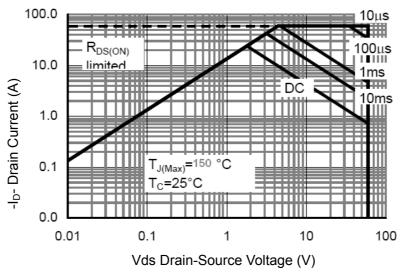


Figure 13 Safe Operation Area

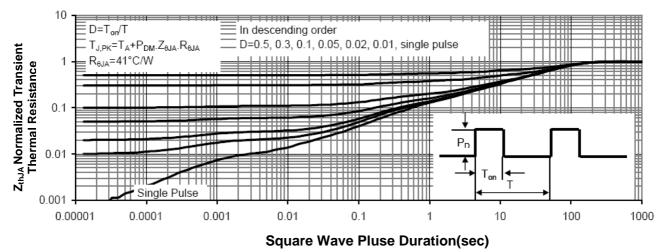
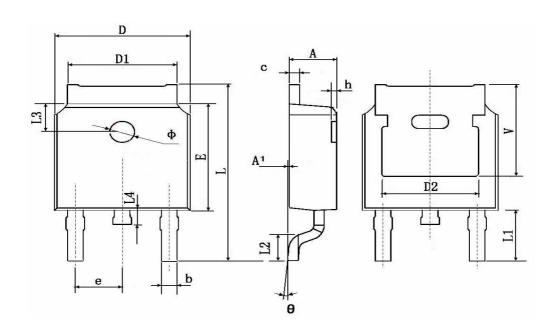


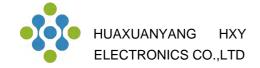
Figure 14 Normalized Maximum Transient Thermal Impedance



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.83	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.90	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP.		0.211 TYP.			



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